IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:	)	
	)	
JUSTIN K. BRASK	)	
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ROBERT S. CHAU	)	
	)	Art Unit: unknown
Serial No.: unknown	)	
	)	Examiner: unknown
Filed: unknown	)	
	)	Attorney Docket: P17280
For: A METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC	)	

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

This Information Disclosure Statement is being submitted under 37 C.F.R. §1.97(b). Enclosed is a copy of Information Disclosure Citation Form PTO-1449 together with copies of the references cited on that form. It is respectfully requested that the cited references be considered and that the enclosed copy of Information Disclosure Citation Form PTO-1449 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

Pursuant to 37 C.F.R. § 1.97, the submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made

and is not to be construed as an admission that the information cited in this statement constitutes prior art or is otherwise material to patentability.

Respectfully submitted,

Dated: August 26, 2003

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August 28, 2003
(Date signed)

LJV/cak (10/01/97)

Form PTO-1449 (Modified)	Atty Docket No.: 42P17280	Serial No.: Unknown
List of Patents and Publications Statement (Use several sheets if necessary)		Applicant: Justin K. Brask et al.
		Filing Date: Herewith

REFERENCE DESIGNATION		U.S. PATENT DOCUMENTS				
Examiner Initials		Document No.		Class	Sub-Class	Filing date if appropriate
	AA	5,625,217	Chau et al.	257	412	
	AB	5,753,560	Hong et al.	438	402	
	AC	5,783,478	Chau et al.	438	592	
	AD	5,891,798	Doyle et al.	438	624	
	AE	6,063,698	Tseng et al.	438	585	
	AF	6,087,261	Nishikawa et al.	438	685	
	AG	6,184,072	Kaushik et al.	438	197	
	AF	6,306,742 B1	Doyle et al.	438	591	
	AI	6,391,802 B1	Delpech et al.	438	785	
	AJ	6,420,279	Ono et al.	48	785	
	AK	6,475,874	Xiang et al.	438	396	
	AL	6,544,906	Rotondaro et al.	438	785	
	AM	US2003/032303	Yu et al.	438	770	

FOREIGN PATENT DOCUMENTS

		Document No.	Date	Country	Class	Sub-Class	Translation
	AM						
	AN						

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

	AO	Doug Barlage et al., "High-Frequency Response of 100nm Integrated CMOS Transistors with High-K Gate Dielectrics", 2001 IEEE, 4 pages.
	AP	Robert Chau et al., "A 50nm Depleted-Substrate CMOS Transistor (DST), 2001 IEEE, 4 pages.
	AQ	Lu et al., "Dual-Metal Gate Technology for Deep-Submicron CMOS Devices", dated April 29, 2003, 1 page.
	AR	Schwantes et al., "Performance Improvement of Metal Gate CMOS Technologies with Gigabit Feature Sizes", Technical University of Hanburg-Harburg, 5 pages.
	AS	Chau et al., "A Method of Making Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/082,530, Filed February 22, 2002
	AT	Parker et al., "A Method of Making Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/285,915, Filed October 31, 2002
	AU	Chau et al., "A Method of Making Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/288,043, Filed November 5, 2002
	AV	Parker et al., "A Method of Making Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/315,268, Filed December 10, 2002
	AW	Doczy et al., "A Method of Making Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/338,174, Filed January 7, 2003
	AX	Brask et al., "A Method of Making Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/387,303, Filed March 11, 2003
	AY	Brask et al., "A Method of Making Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/391,816, Filed March 18, 2003
	AZ	Chau et al., "A Method for Making a Semiconductor Device Having a Metal Gate Electrode", Serial No. 10/431,166, Filed May 6, 2003
	BA	Brask, et al, "A Method for Making a Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/441,616, filed May 20, 2003

Examiner	Date Considered

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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